RT3Y97M

Composite Transistor For Muting Application

DESCRIPTION

RT3Y97M is a composite transistor built with RT1P140 and two muting transistor with resistor in SC-88 package.

FEATURE

•RT3Y97M is built in RTr1 side RT1P140,and RTr2,RTr3 side composite muting transistor with resistor.

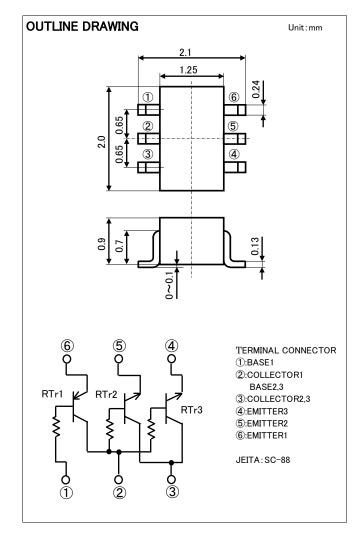
•Built-in bias resistor

 $RTr1:R_1=10k\Omega$ $RTr2,RTr3:R_1=2.2k\Omega$

•Mini package for easy mounting

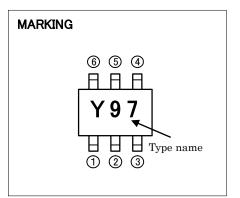
APPLICATION

muting circuit, switching circuit



MAXIMUM RATING (Ta=25°C)

SYMBOL	PARAMETER	RTr1 RATING	RTr2,RTr3 RATING	UNIT	
V _{CBO}	Collector to Base voltage	-9	40	V	
V _{EBO}	Emitter to Base voltage	-50	40	V	
V _{CEO}	Collector to Emitter voltage	-9	15	V	
Ic	Collector current	-100	200	mA	
Ρτ	Total dissipation	15	mW		
Tj	Junction temperature	+1	°C		
T_{stg}	Storage temperature	-55~	°C		



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ELECTRICAL CHARACTERISTICS (Ta=25°C) (RTr1side)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Тур	Max	Unit
V _{CBO}	Collector-base breakdown voltage	$I_c=-50\mu A$, $I_E=0mA$	-9	Ι	_	V
V_{EBO}	Emitter-base breakdown voltage	I_{E} =-50µA, I_{C} =0mA	-50	Ι	-	V
V _{CEO}	Collector-emitter breakdown voltage	I _C =−1mA, R _{BE} =∞	-9	-	-	V
I _{CBO}	Collector cutoff current	V_{CB} =-6V, I _E =0mA	-	Ι	-0.1	μA
I _{EBO}	Emitter cutoff current	V_{EB} =-50V, I_{C} =0mA	-	-	-0.1	μA
h _{FE}	DC current transfer ratio	V_{CE} =-5V, I _C =-1mA	-	10	-	-
R ₁	Input resistance	-	I	10	-	kΩ

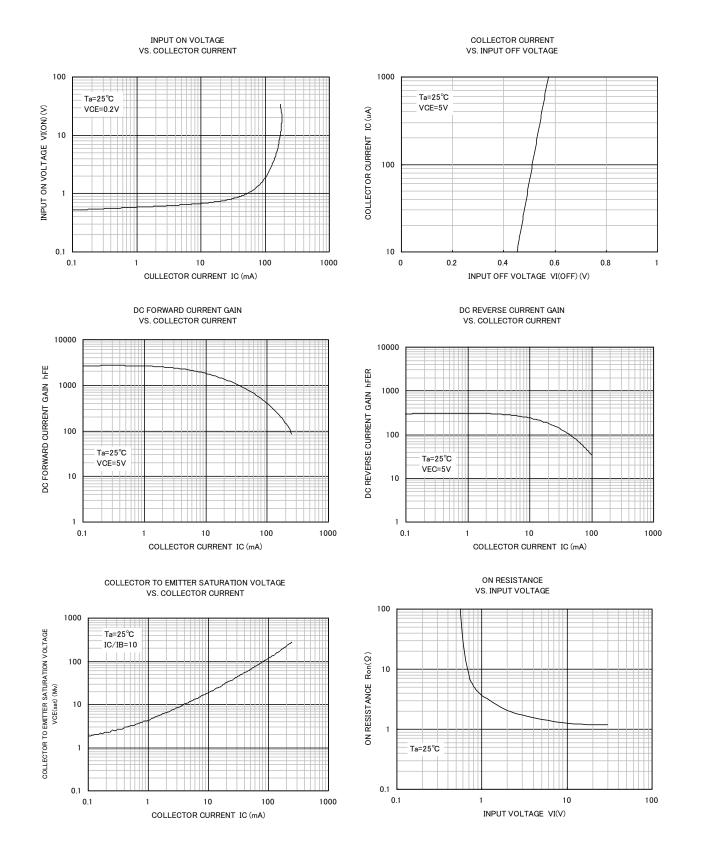
ELECTRICAL CHARACTERISTICS (Ta=25°C) (RTr2,RTr3 common)

Symbol	Parameter	Test conditions	Limits			11
			Min	Тур	Max	Unit
V _{CBO}	Collector-base breakdown voltage	I_{C} =50µA, I_{E} =0mA	40	-	-	V
V_{EBO}	Emitter-base breakdown voltage	$I_E=50\mu A$, $I_C=0mA$	40	-	-	V
V_{CEO}	Collector-emitter breakdown voltage	I _C =1mA, R _{BE} =∞	15	-	-	V
\mathbf{I}_{CBO}	Collector cutoff current	V _{CB} =40V, I _E =0mA	-	-	0.5	μA
\mathbf{I}_{EBO}	Emitter cutoff current	V_{EB} =40V, I _C =0mA	-	-	0.5	μA
h _{FE}	DC current transfer ratio	V_{CE} =5V, I _C =10mA	820	-	2500	-
$V_{\text{CE}(\text{sat})}$	Collector-emitter saturation voltage	I_{C} =50mA, I_{B} =5mA	-	-	100	mV
R ₁	Input resistance	-	-	2.2	-	kΩ
f⊤	Transition frequency	V _{CE} =6V, I _E =-10mA	-	60	-	MHz
Ron	Output On-resistance	V _{IN} =3V, f=1MHz	-	1.6	-	Ω



Composite Transistor For Muting Application

TYPICAL CHARACTERISTICS (RTr2,RTr3)



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